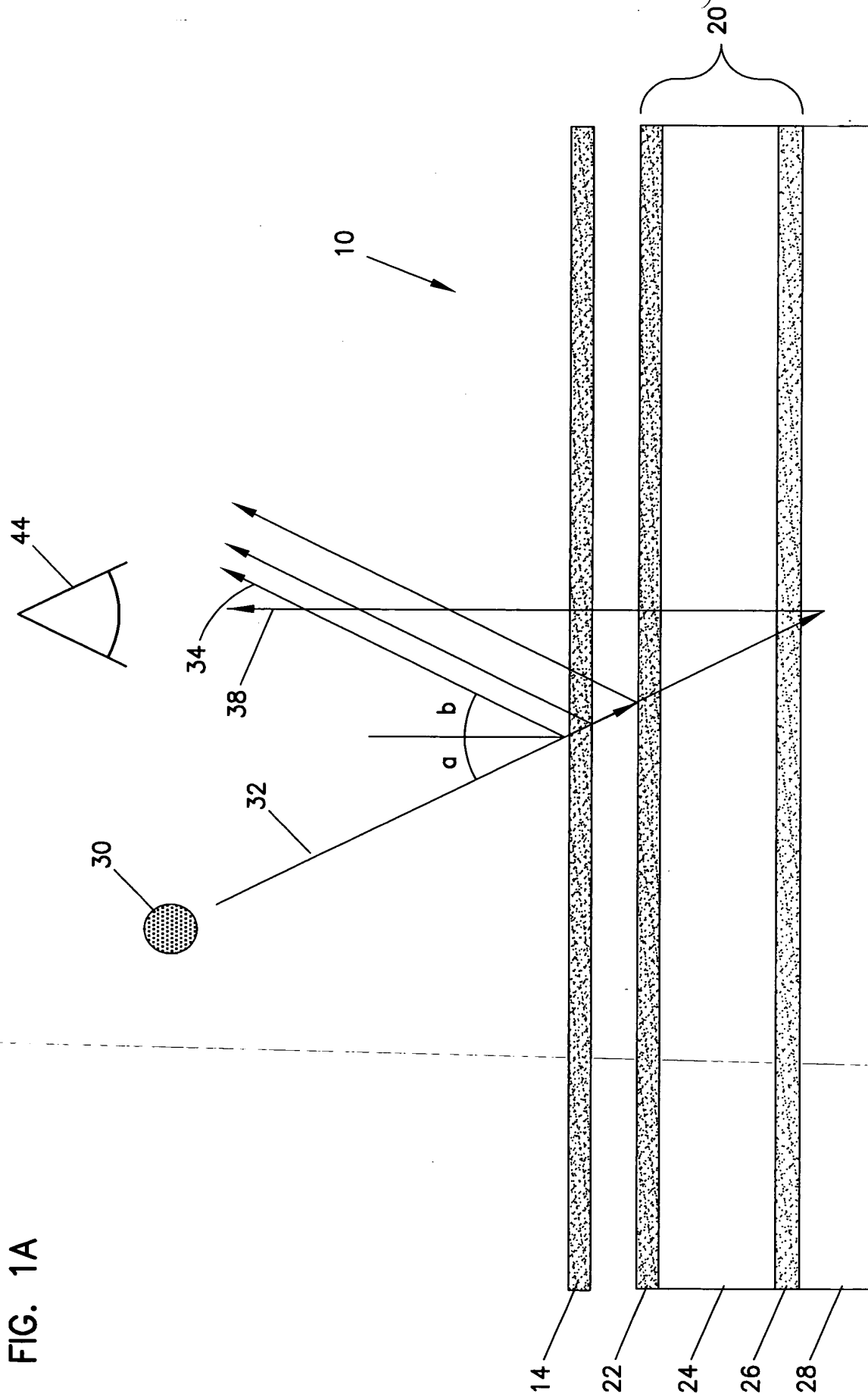
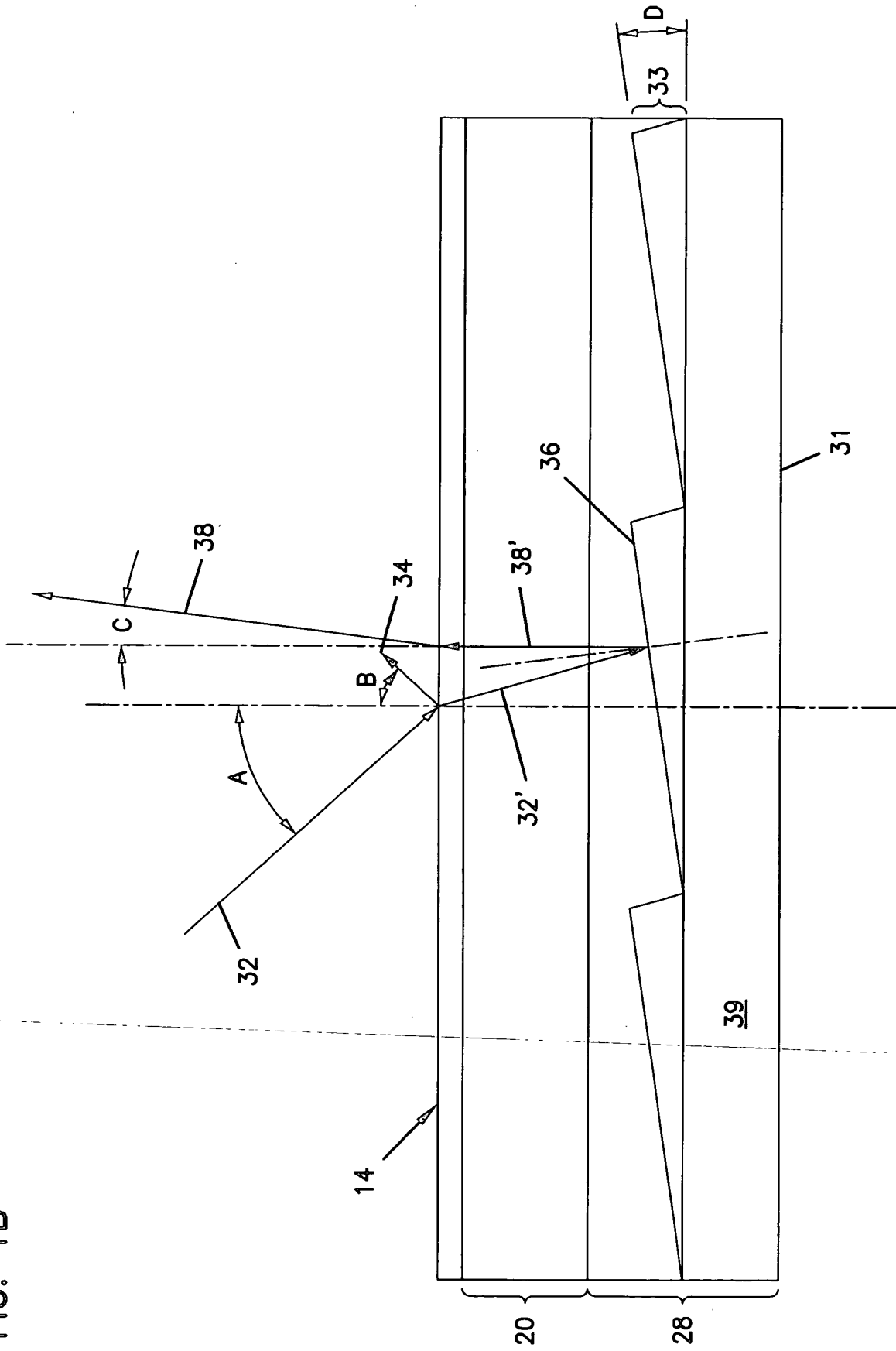


FIG. 1A





TOP SECRET 8E422600

FIG. 2A

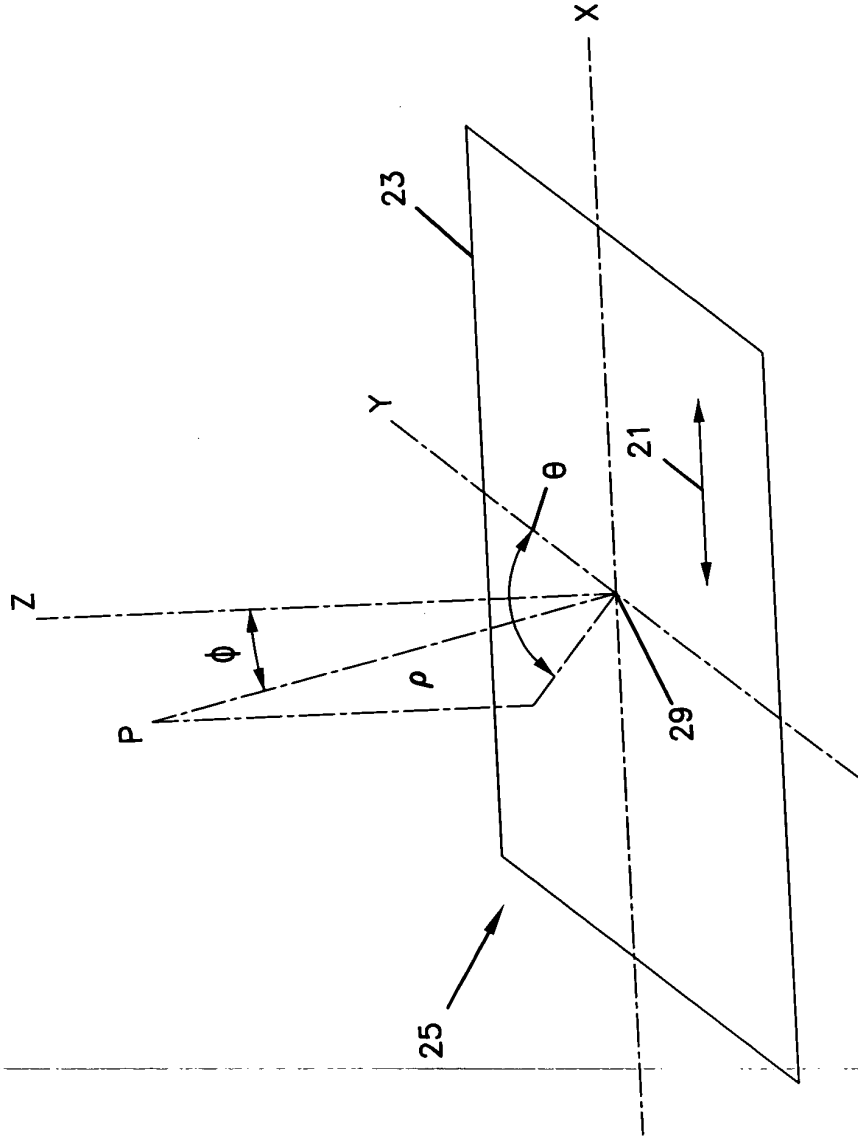
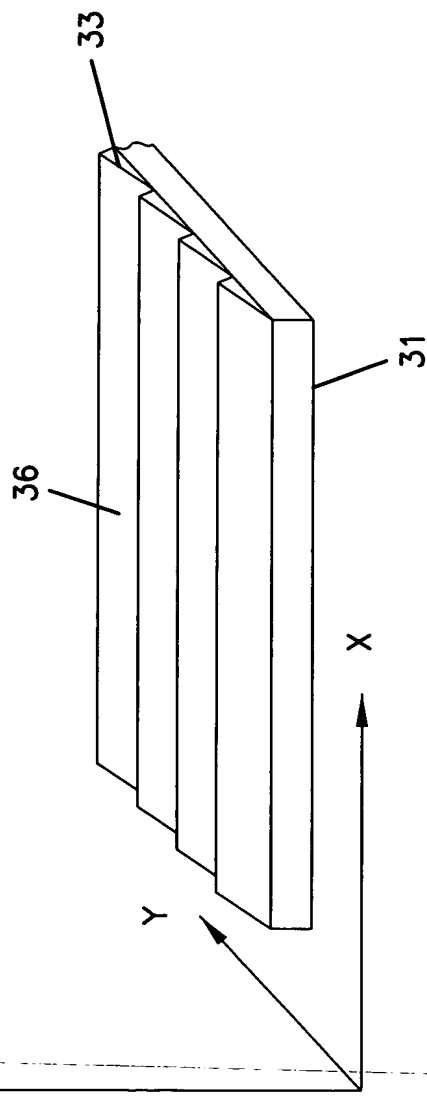


FIG. 2B



106007-8E422660

TOP OF SHEET 5

FIG. 2C

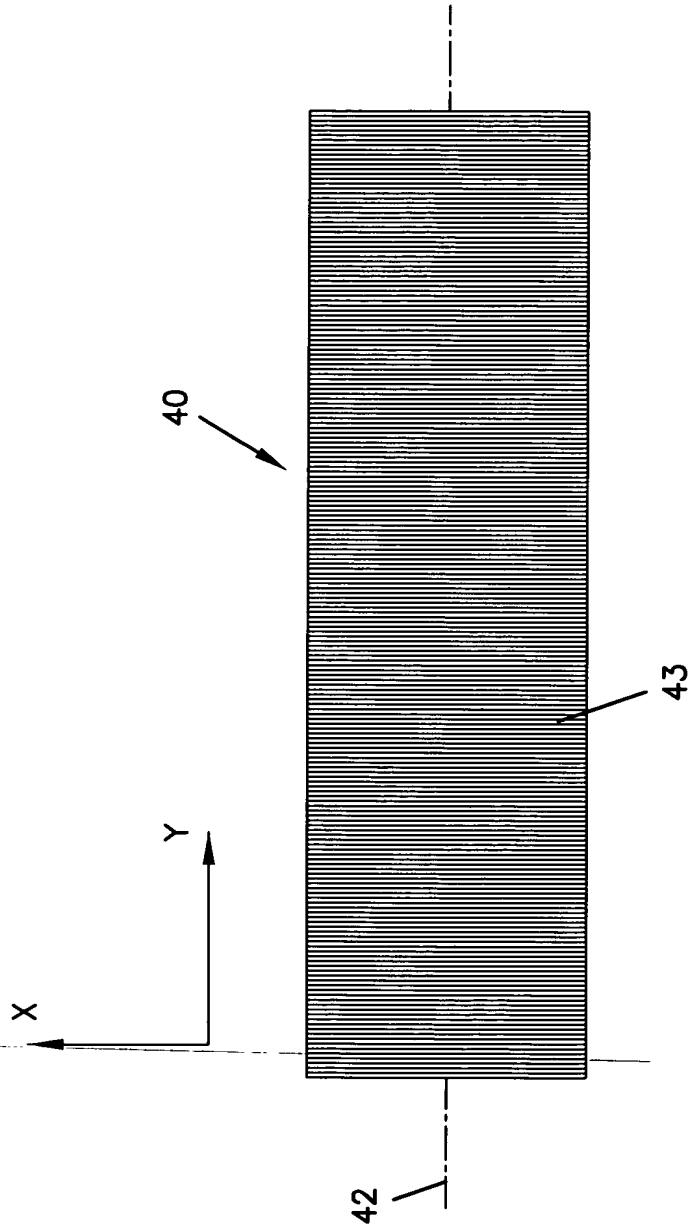


FIG. 3

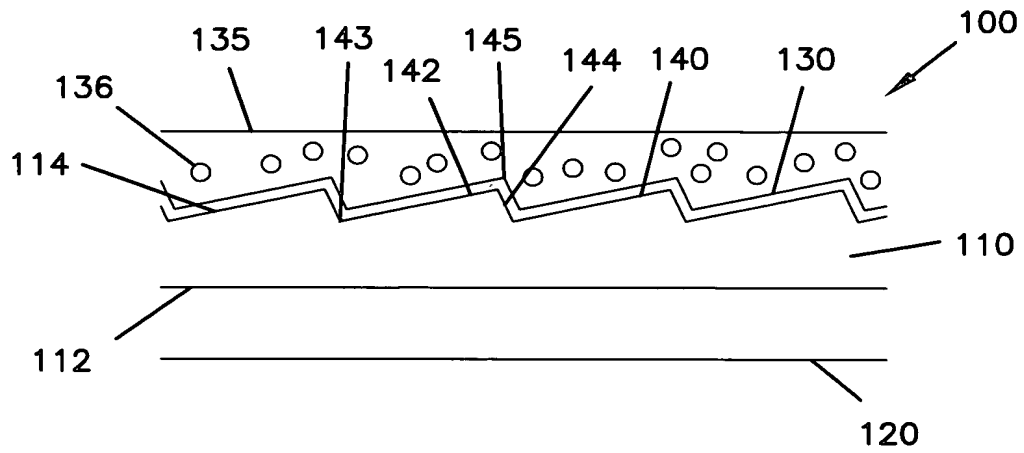


FIG. 5

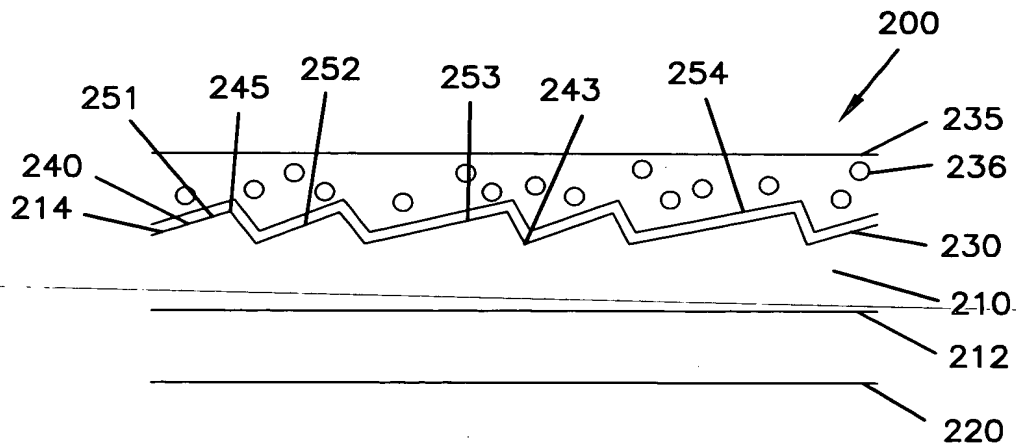
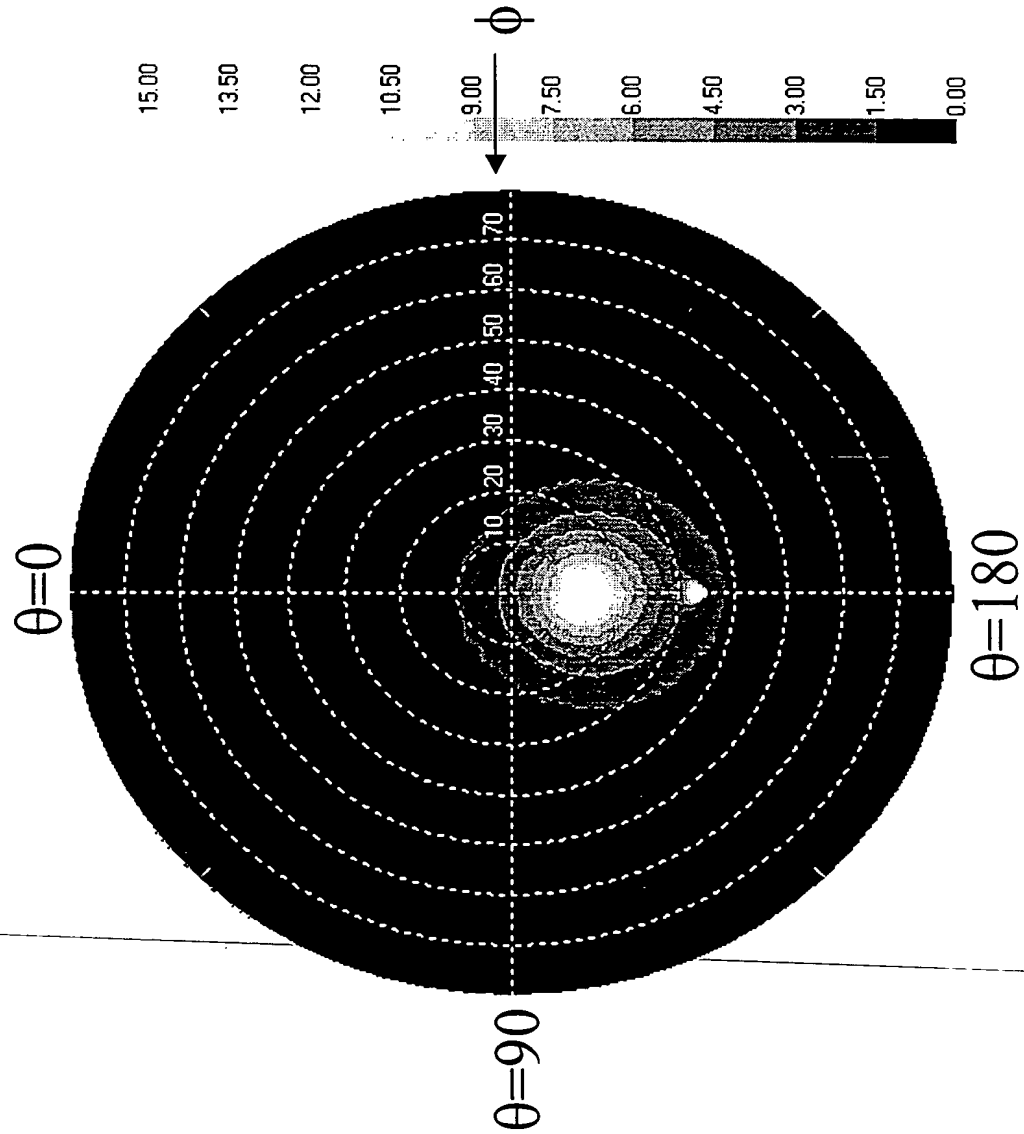


FIG. 4



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A cross-sectional view of a multi-layered structure 300. The structure consists of a top layer 335, a middle layer 330, and a bottom layer 310. The middle layer 330 contains a series of circular features 340, 343, 342, 344, and 345. The bottom layer 310 has a wavy, undulating profile. Below the main structure 300, there are two additional layers, 312 and 320, which are shown as flat horizontal lines.

This diagram shows a cross-sectional view of a semiconductor device. A wavy interface separates a top layer from a bottom layer. The top layer contains several small circles. The bottom layer is divided into two horizontal sections by a dashed line. Various components are labeled with reference numerals: 400 points to the top surface, 410 to the wavy interface, 412 to the top horizontal section, 414 to the bottom horizontal section, 420 to the bottom layer, 430 to a circle, 435 to a circle, 436 to a circle, 440 to a circle, 442 to a circle, 443 to a circle, 444 to a circle, 445 to a circle, and 446 to a circle.

FIG. 7

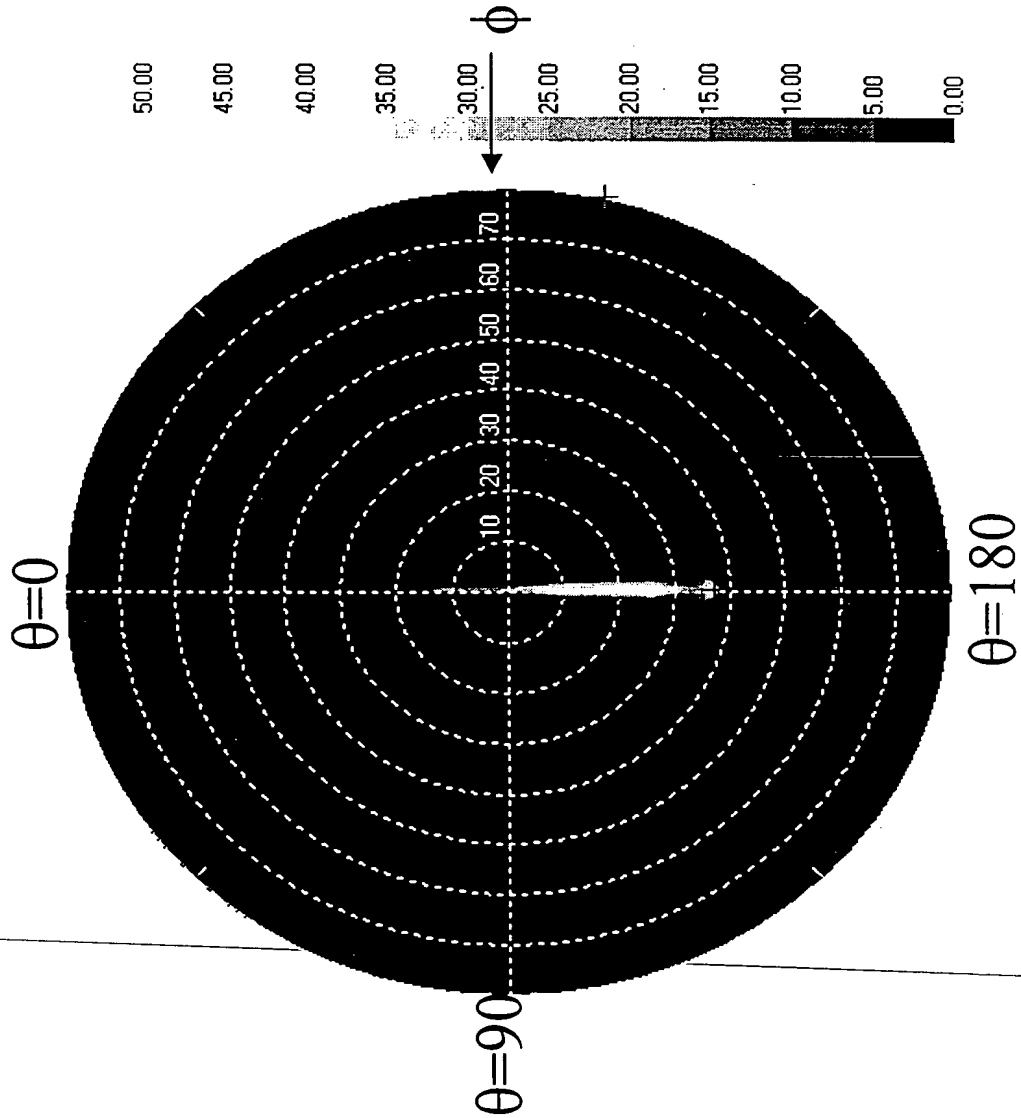
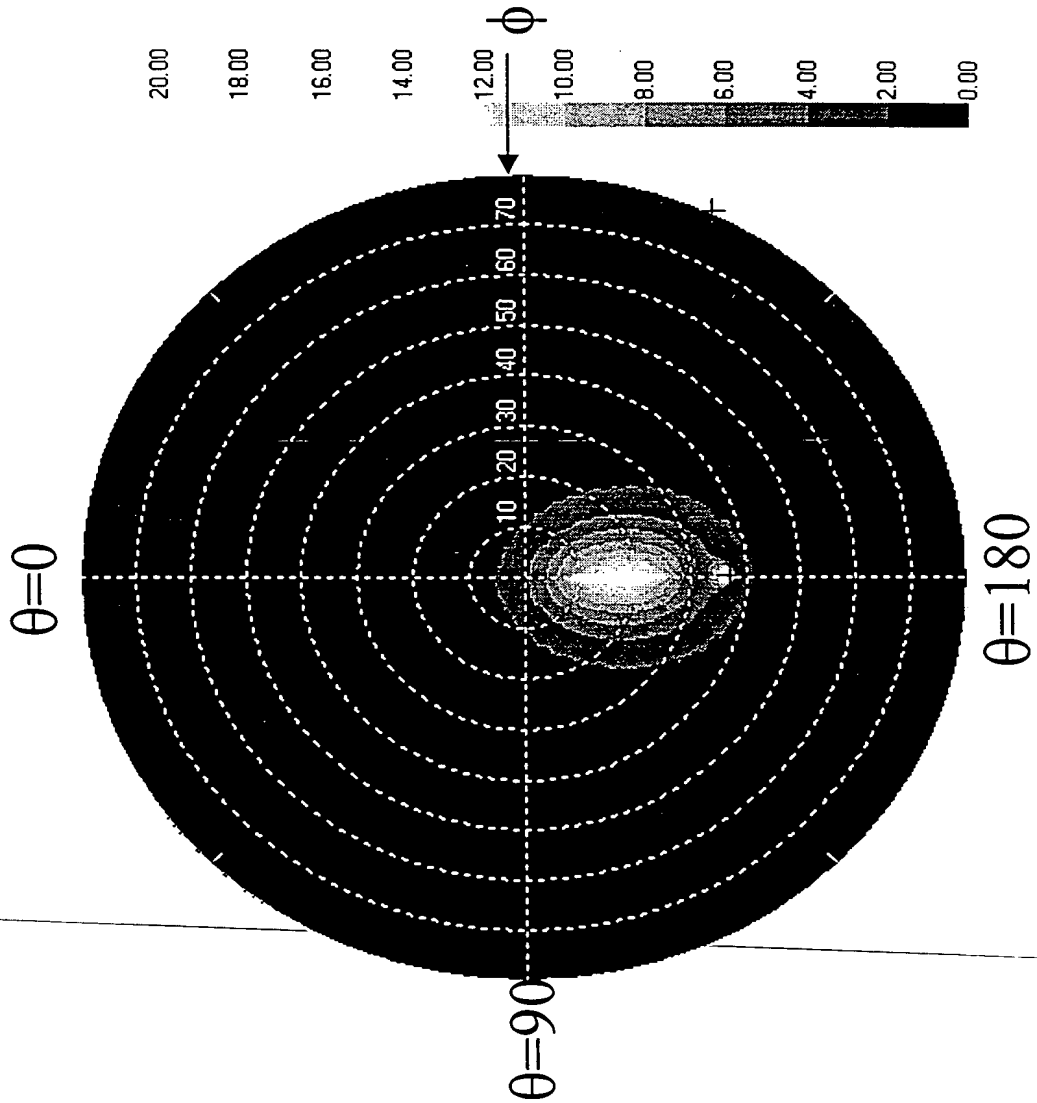


FIG. 7

FIG. 8



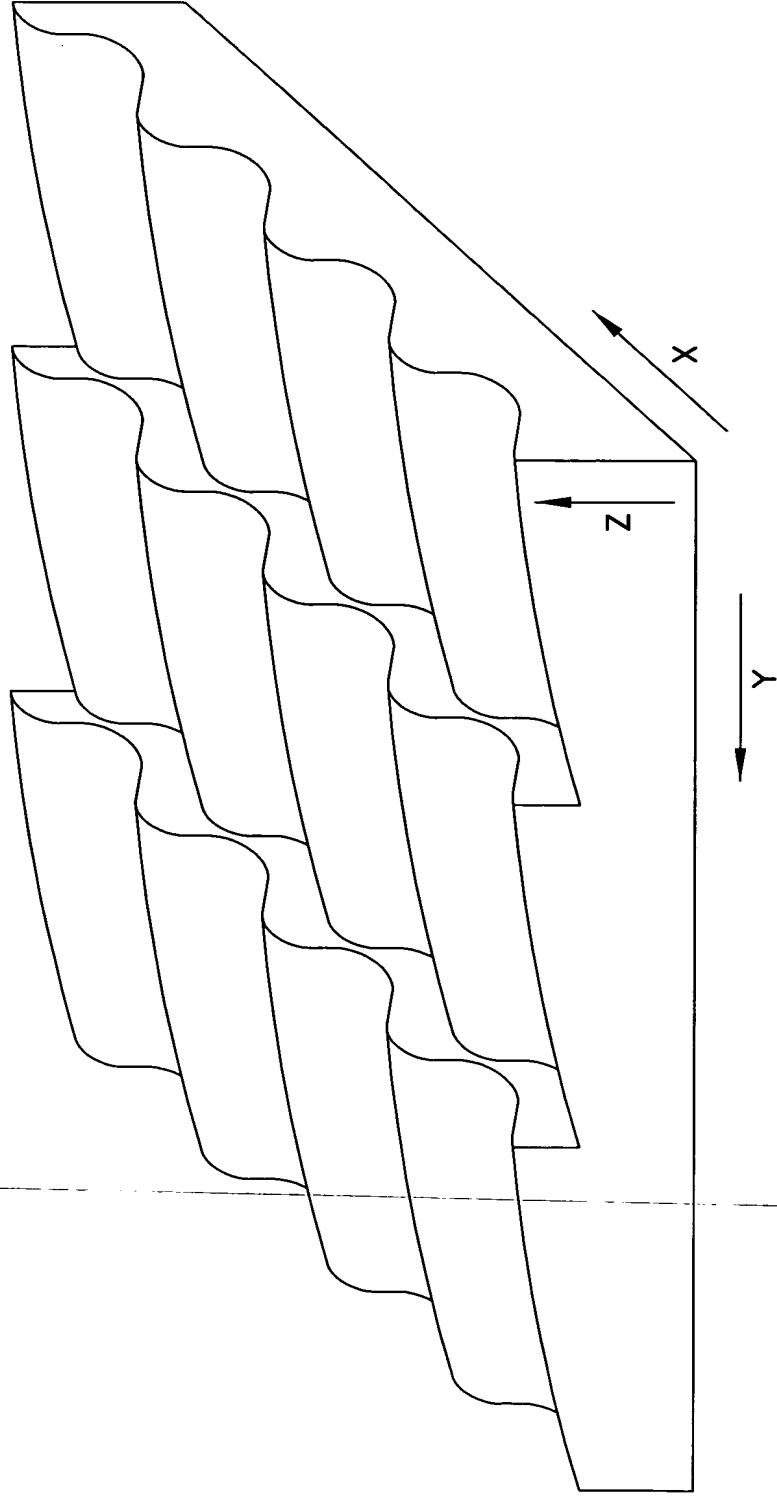


FIG. 10A

FIG. 10A

FIG. 10B

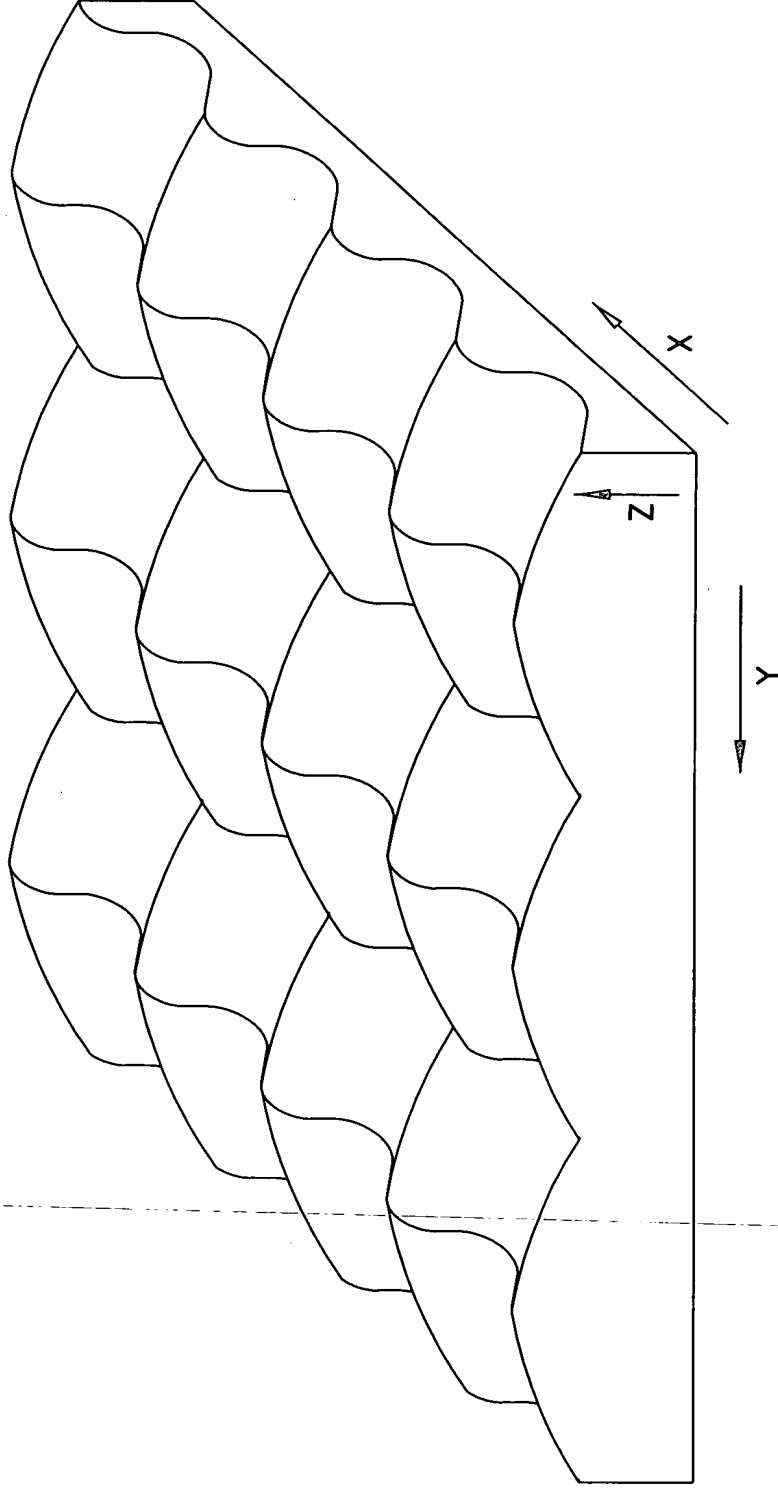
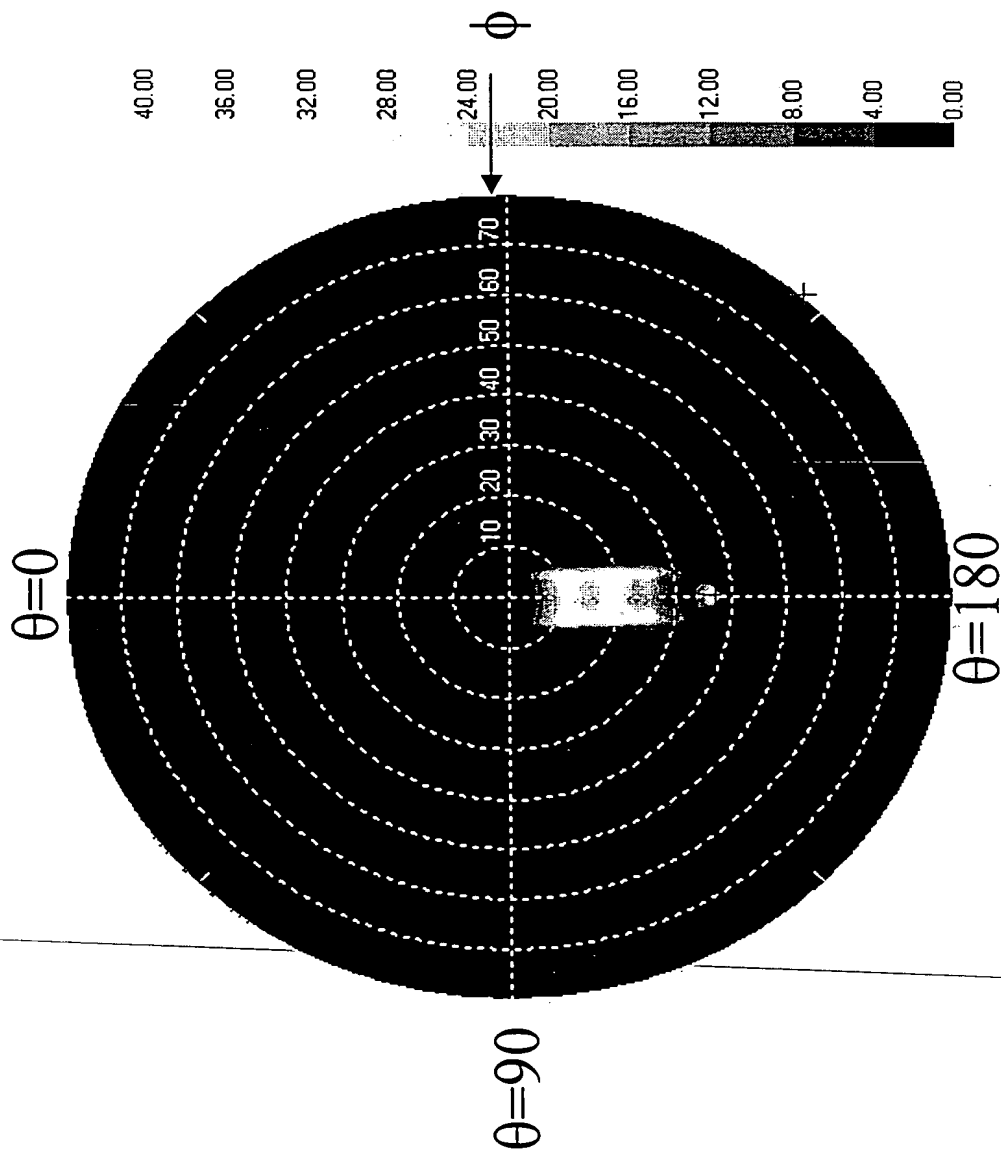


FIG. 10B

FIG. 11



T0600T* 3E422660

FIG. 12

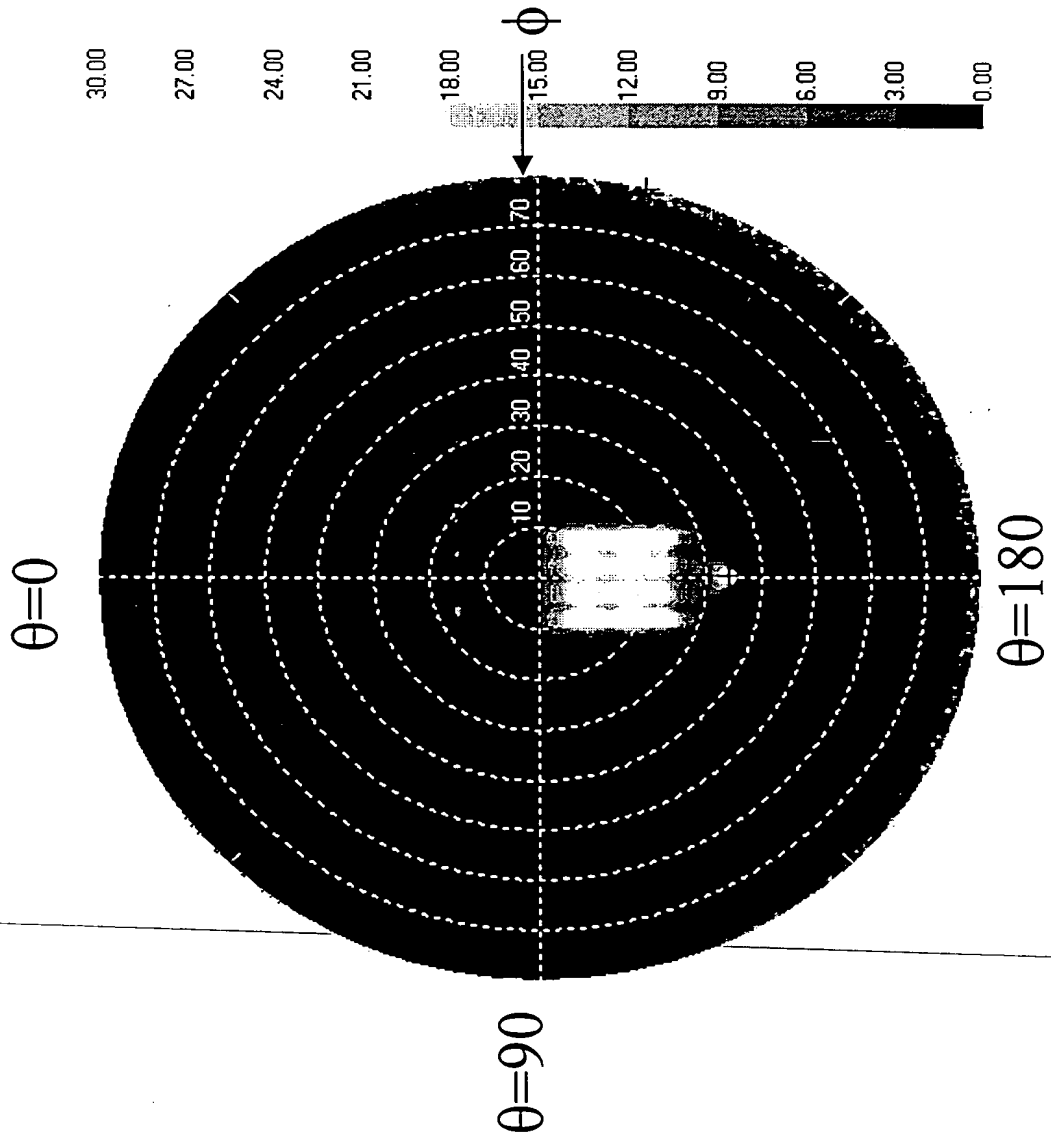


FIG. 13

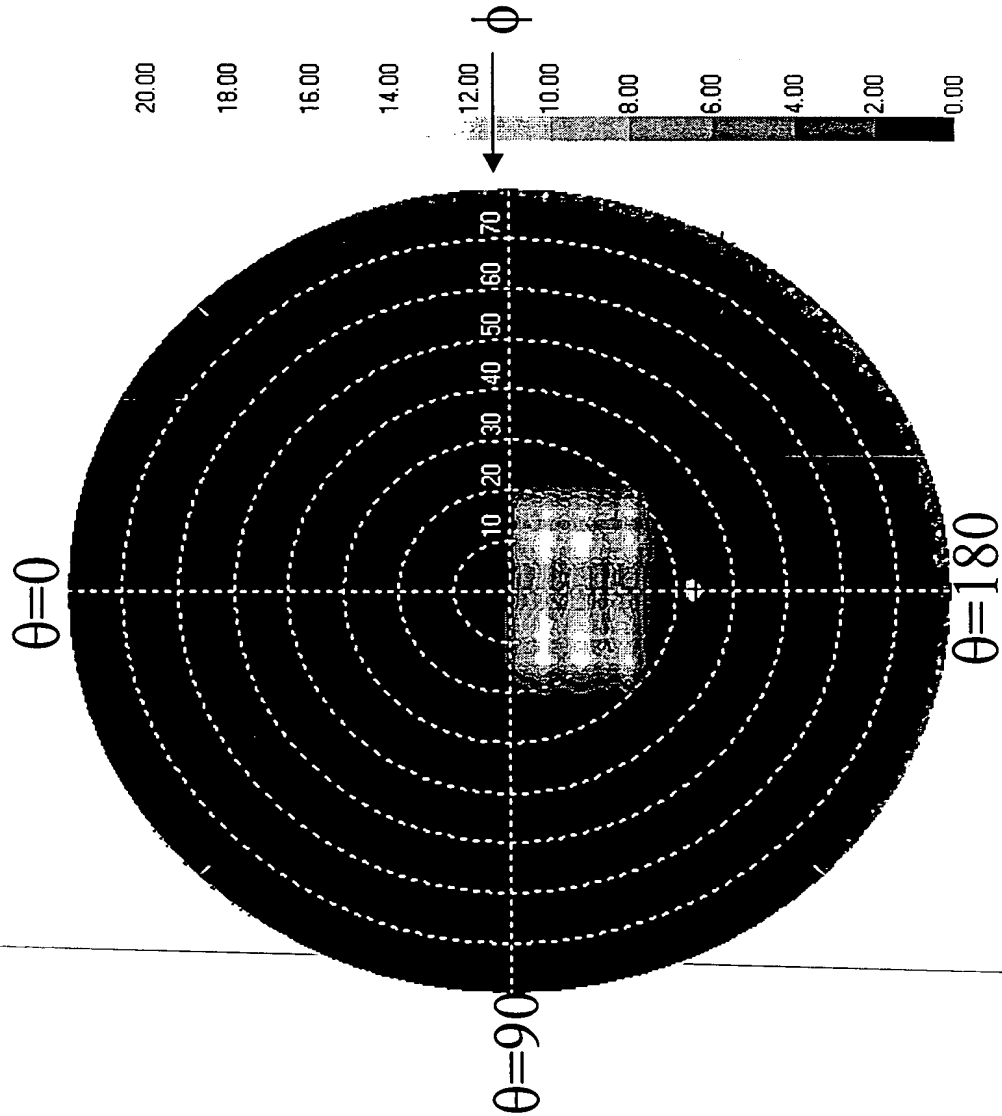
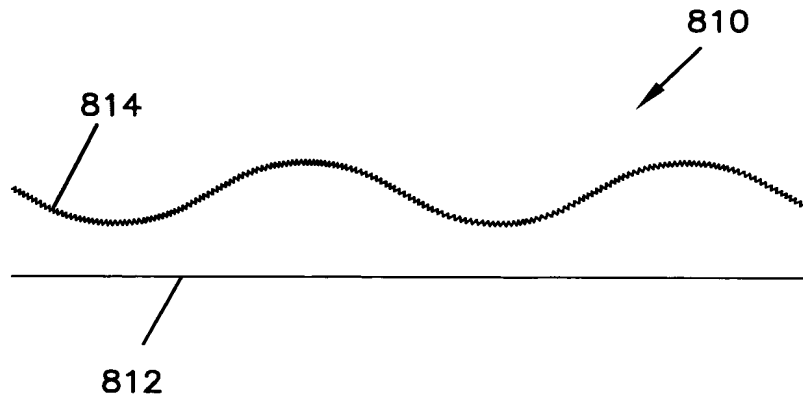
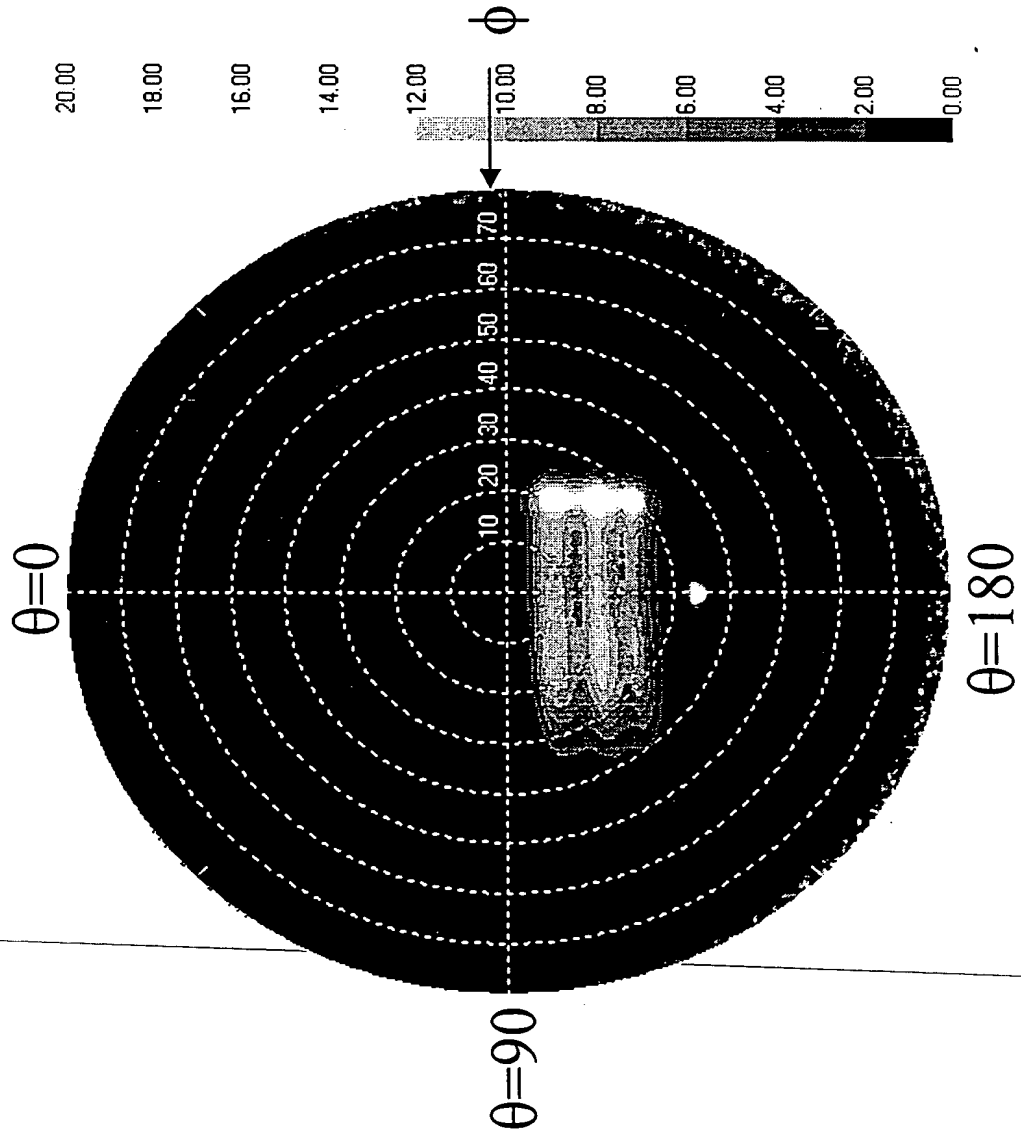


FIG. 14



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FIG. 15



T0600T" BEH22660

FIG. 16

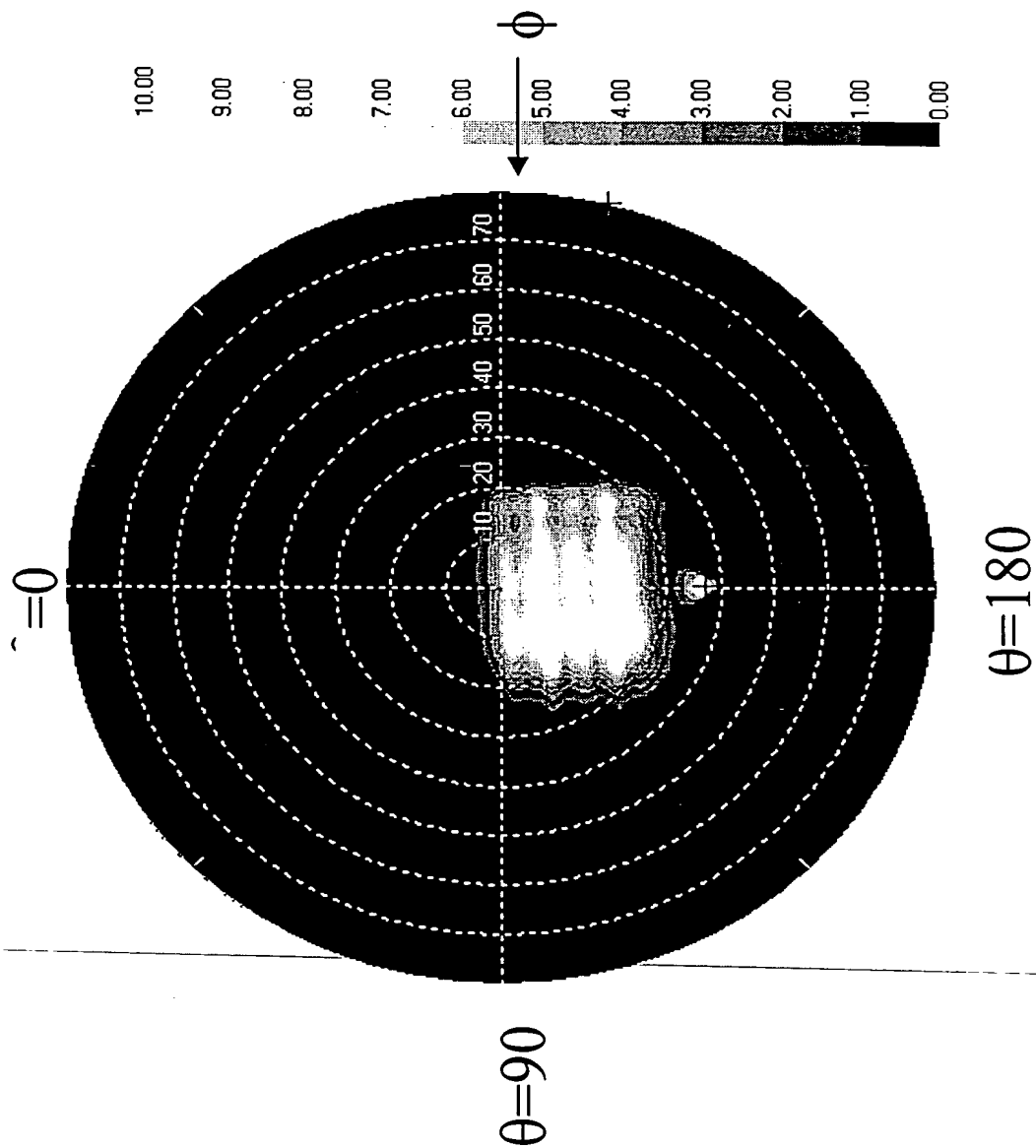


FIG. 17

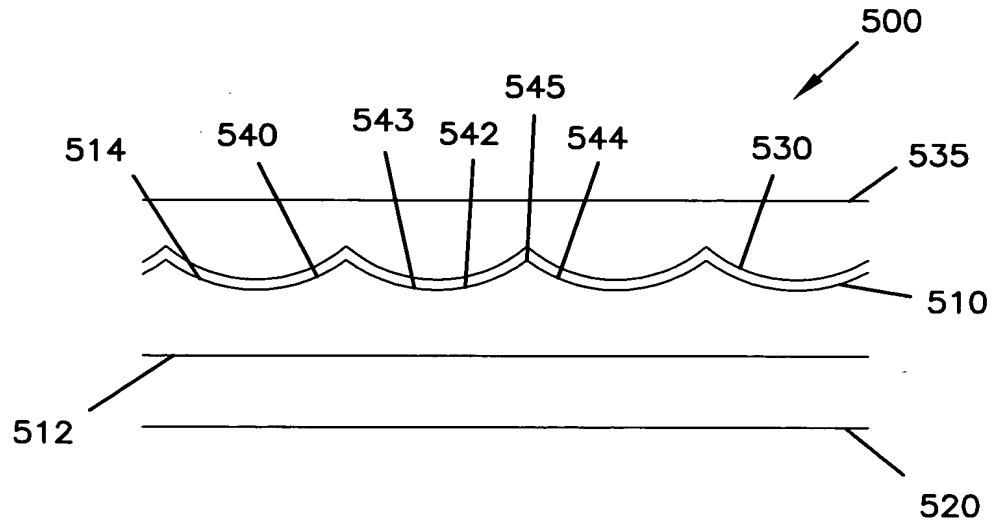
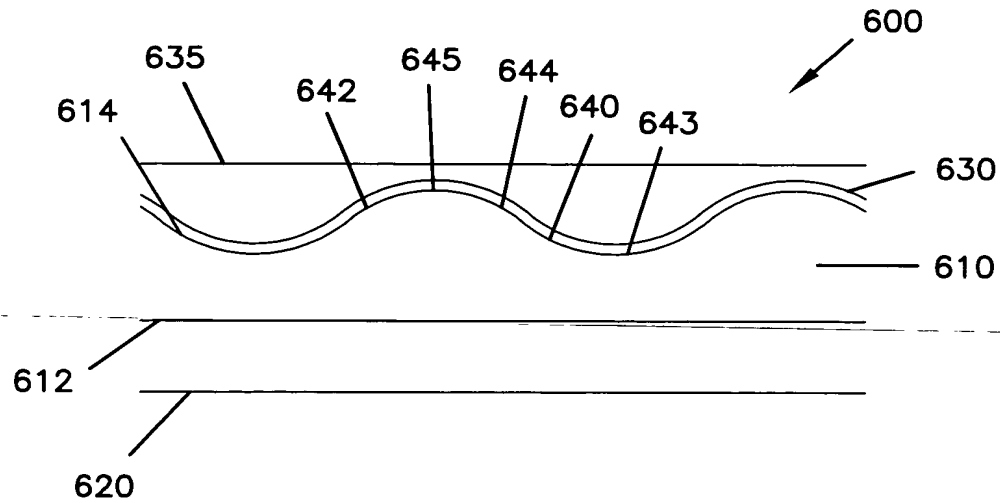


FIG. 18



0902438-10001

15:07
8-APR-61

3
4
2
44
2
1 A
M JZ
AOC
EOP

5. 2. 4. 9. 2. 3.

Fig. 19

FOOT" BEH22650

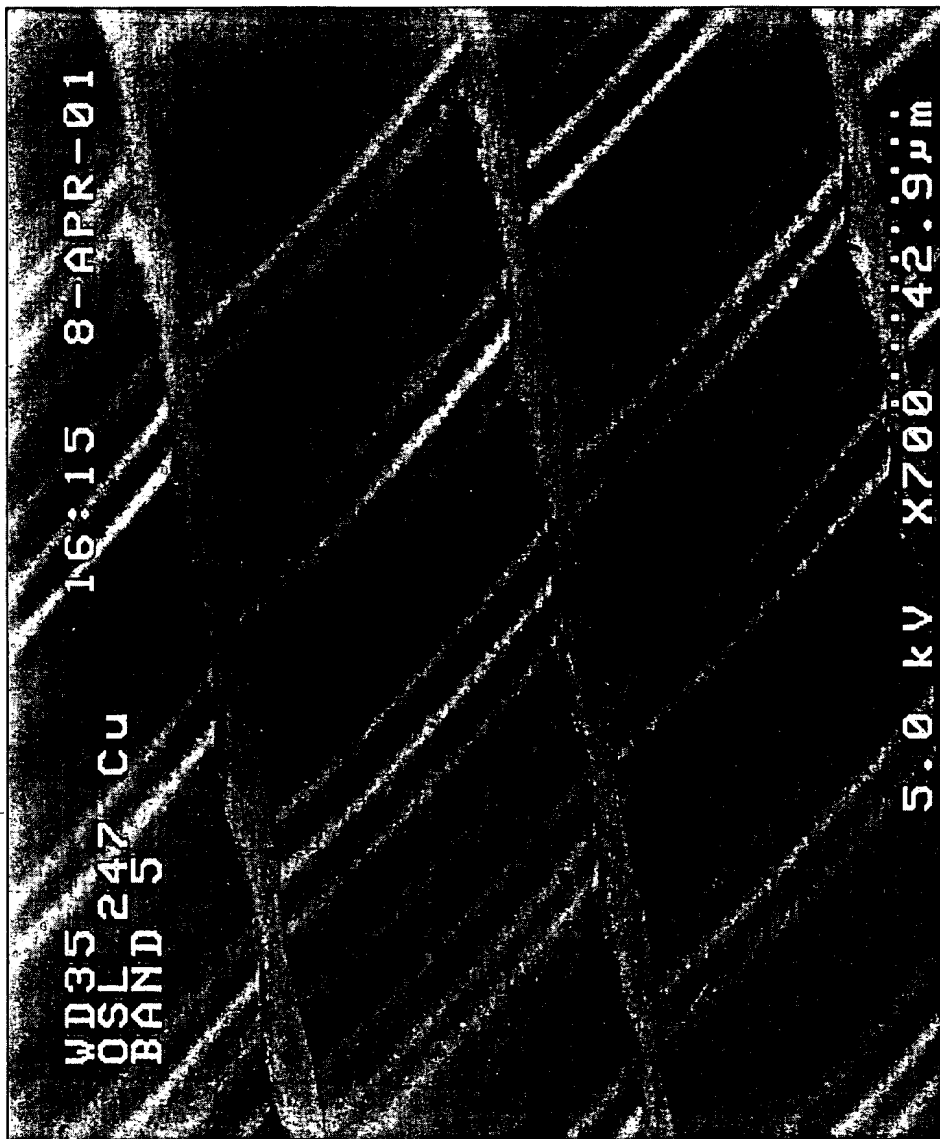
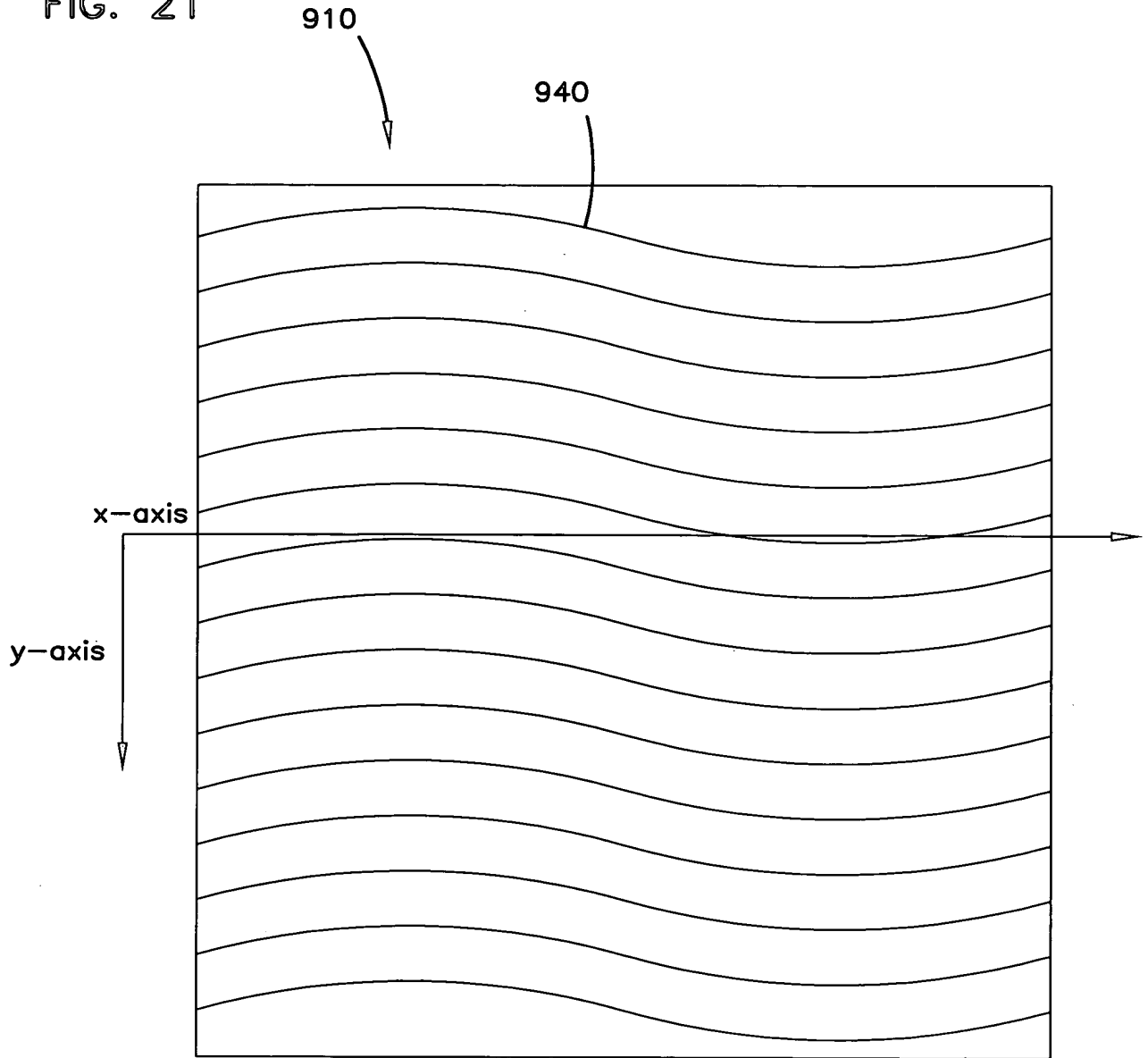


FIG. 20

FIG. 21



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FIG. 22

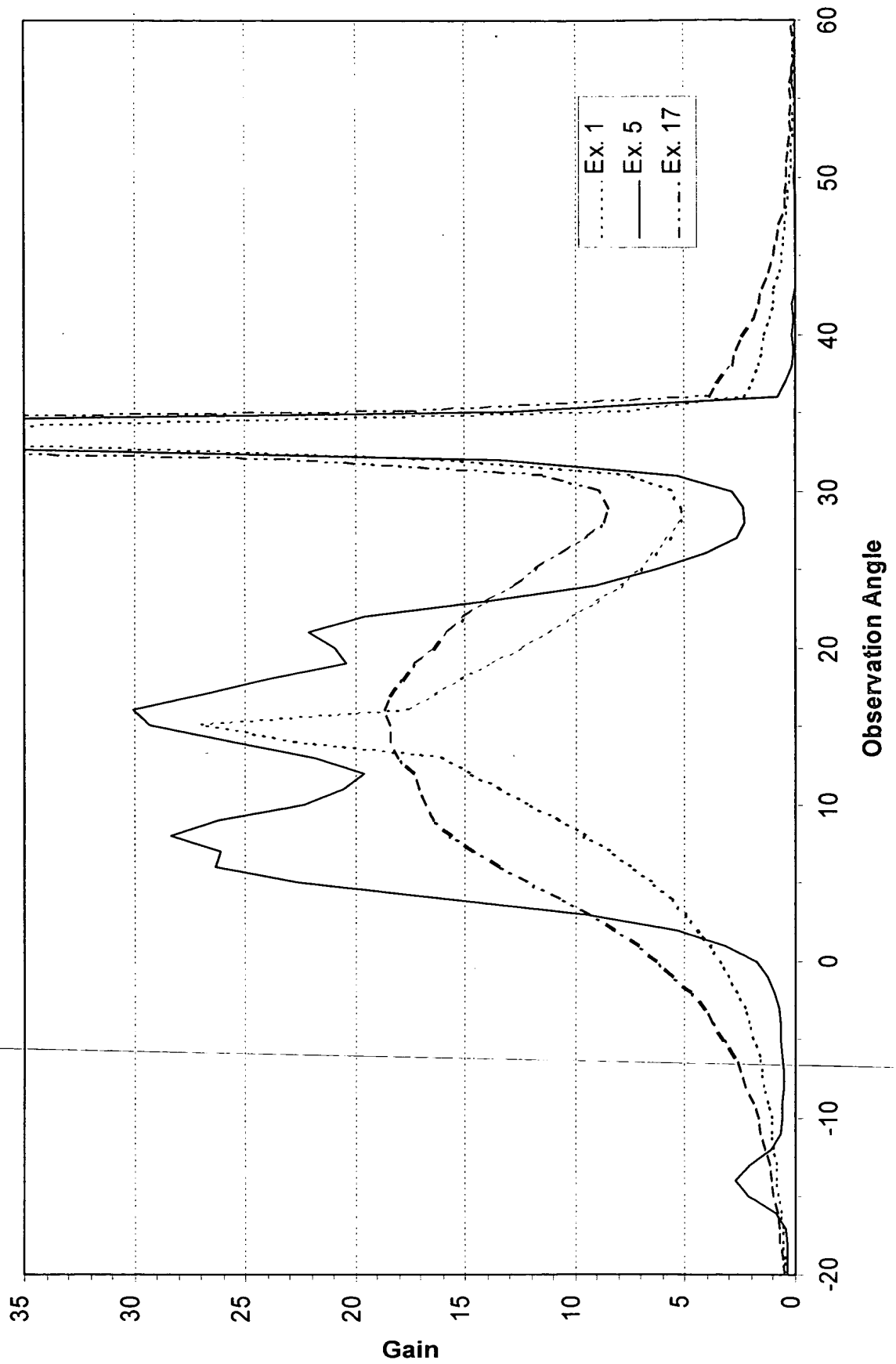


FIG. 22